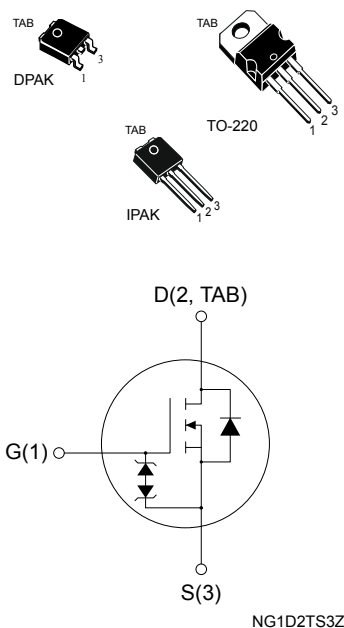


N-channel 650 V, 0.60 Ω typ., 7 A MDmesh™ M2 Power MOSFET in DPAK, TO-220 and IPAK packages



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}	Package
STD11N65M2	650 V	0.68 Ω	7 A	85 W	DPAK
STP11N65M2					TO-220
STU11N65M2					IPAK

- Extremely low gate charge
- Excellent output capacitance (C_{OSS}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the MDmesh M2 technology. Thanks to their strip layout and improved vertical structure, these devices exhibit low on-resistance and optimized switching characteristics, rendering them suitable for the most demanding high-efficiency converters.



Product status link

[STD11N65M2](#)
[STP11N65M2](#)
[STU11N65M2](#)

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_{case} = 25\text{ }^{\circ}\text{C}$	7	A
	Drain current (continuous) at $T_{case} = 100\text{ }^{\circ}\text{C}$	4.4	
$I_{DM}^{(1)}$	Drain current (pulsed)	28	A
P_{TOT}	Total power dissipation at $T_{case} = 25\text{ }^{\circ}\text{C}$	85	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
T_j	Operating junction temperature range		

1. Pulse width limited by T_{jmax} .
2. $I_{SD} \leq 7\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS}(\text{peak}) \leq V_{(BR)DSS}$, $V_{DS} = 400\text{ V}$
3. $V_{DS} \leq 520\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value			Unit
		DPAK	TO-220	IPAK	
$R_{thj-case}$	Thermal resistance junction-case	1.47			$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient		62.5	100	
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50			

1. When mounted on a 1-inch² FR-4, 2 Oz copper board.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
$I_{AR}^{(1)}$	Avalanche current, repetitive or not repetitive	1.5	A
$E_{AS}^{(2)}$	Single pulse avalanche energy	110	mJ

1. Pulse width limited by T_{jmax} .
2. starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$.

2 Electrical characteristics

($T_{case} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_{case} = 125\text{ }^{\circ}\text{C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 3.5\text{ A}$		0.60	0.68	Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	410	-	pF
C_{oss}	Output capacitance		-	20	-	
C_{rss}	Reverse transfer capacitance		-	0.9	-	
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0\text{ V}$	-	43	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	6.4	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 7\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 16)	-	12.5	-	nC
Q_{gs}	Gate-source charge		-	3.2	-	
Q_{gd}	Gate-drain charge		-	5.8	-	

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 3.5\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 15 and Figure 20)	-	9.5	-	ns
t_r	Rise time		-	7.5	-	
$t_{d(off)}$	Turn-off delay time		-	26	-	
t_f	Fall time		-	15	-	

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		7	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		28	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 7\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 17)	-	318		ns
Q_{rr}	Reverse recovery charge		-	2.5		μC
I_{RRM}	Reverse recovery current		-	15.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17)	-	437		ns
Q_{rr}	Reverse recovery charge		-	3.2		μC
I_{RRM}	Reverse recovery current		-	15		A

1. Pulse width is limited by safe operating area.

2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

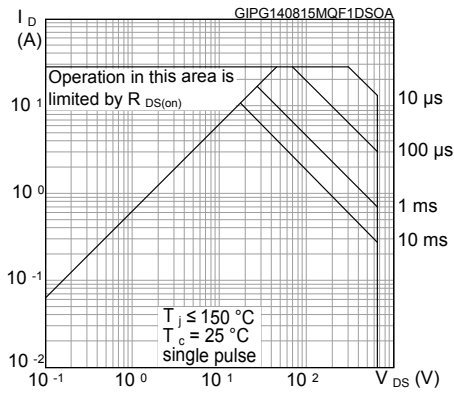
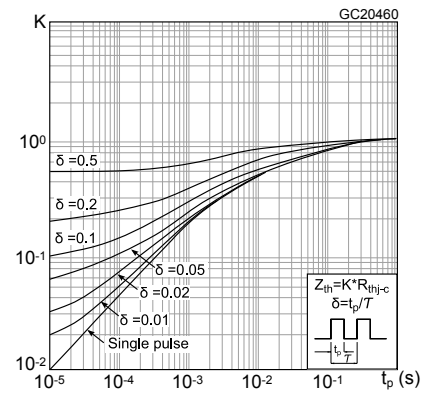
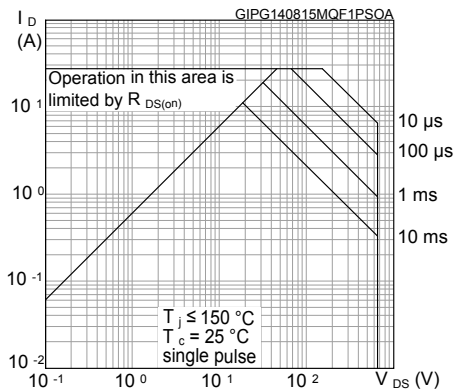
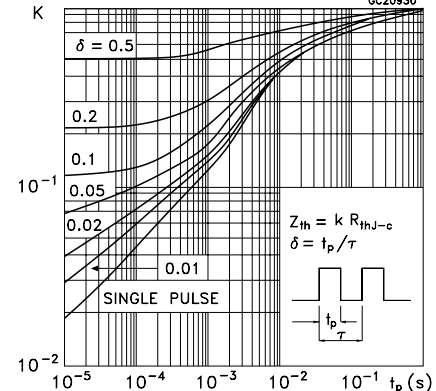
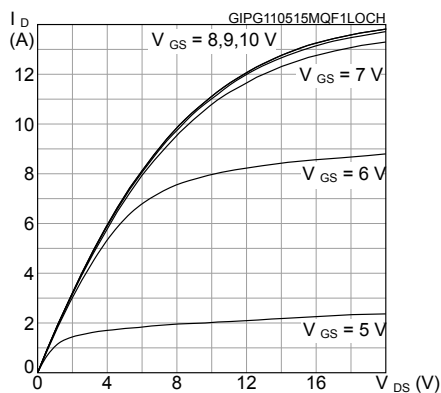
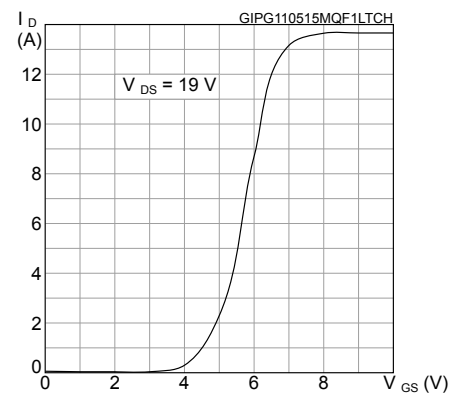
Figure 1. Safe operating area for DPAK and IPAK

Figure 2. Thermal impedance for DPAK and IPAK

Figure 3. Safe operating area for TO-220

Figure 4. Thermal impedance for TO-220

Figure 5. Output characteristics

Figure 6. Transfer characteristics


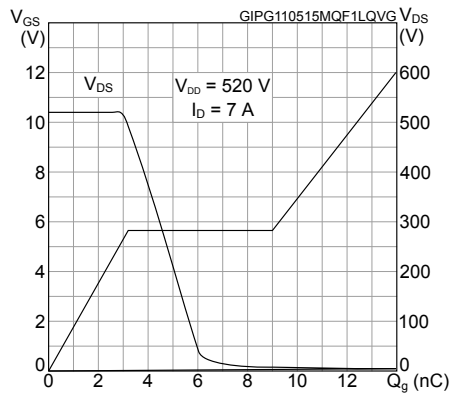
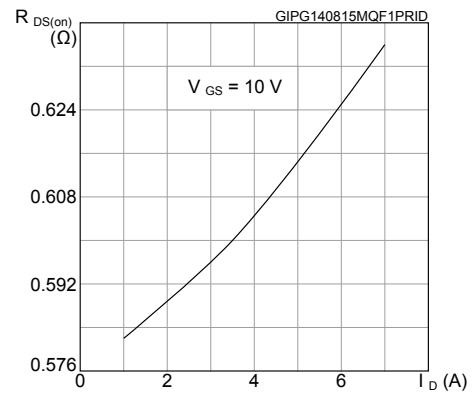
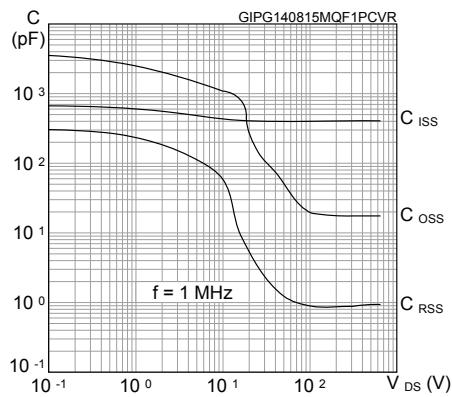
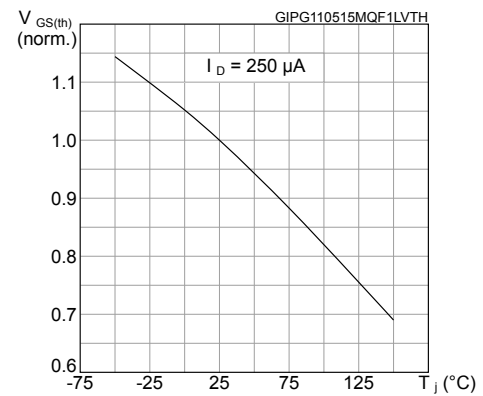
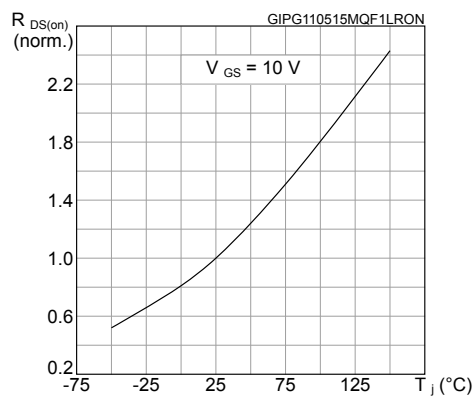
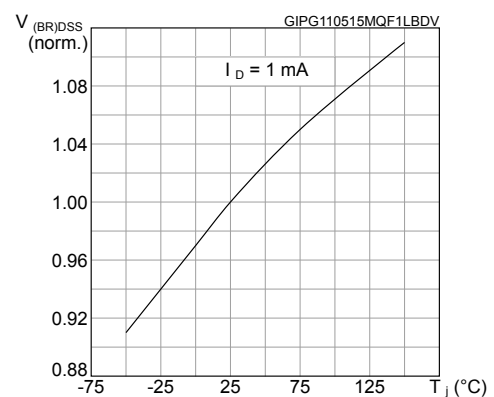
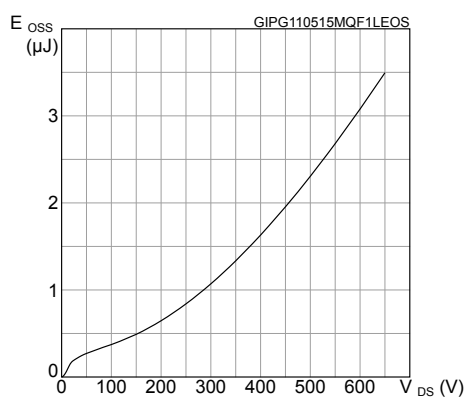
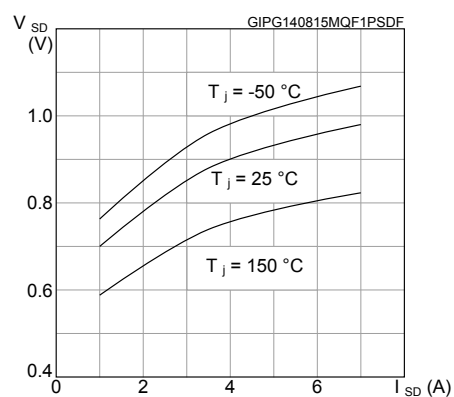
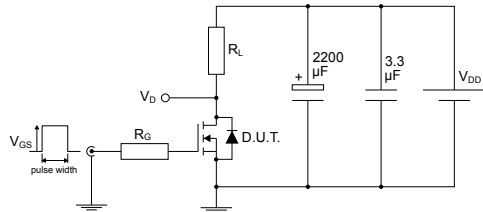
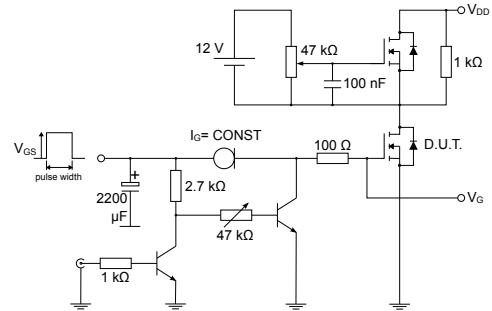
Figure 7. Gate charge vs gate-source voltage

Figure 8. Static drain-source on-resistance

Figure 9. Capacitance variations

Figure 10. Normalized gate threshold voltage vs temperature

Figure 11. Normalized on-resistance vs temperature

Figure 12. Normalized $V_{(BR)DSS}$ vs temperature


Figure 13. Output capacitance stored energy

Figure 14. Source-drain diode forward characteristics


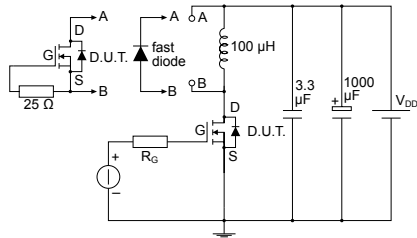
3 Test circuits

Figure 15. Test circuit for resistive load switching times


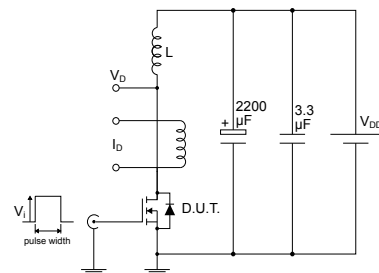
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Figure 16. Test circuit for gate charge behavior


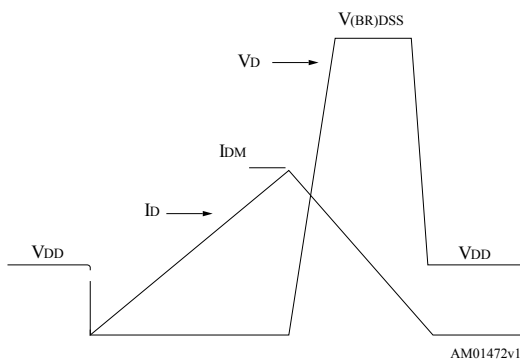
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Figure 17. Test circuit for inductive load switching and diode recovery times


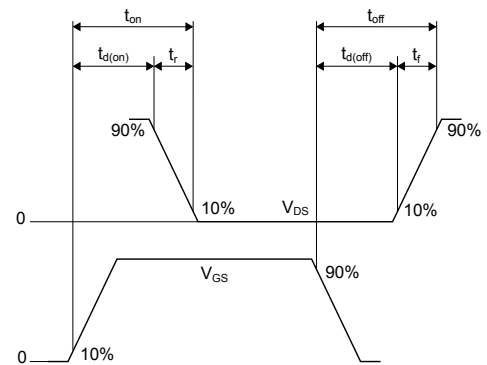
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Figure 18. Unclamped inductive load test circuit


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Figure 19. Unclamped inductive waveform


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Figure 20. Switching time waveform


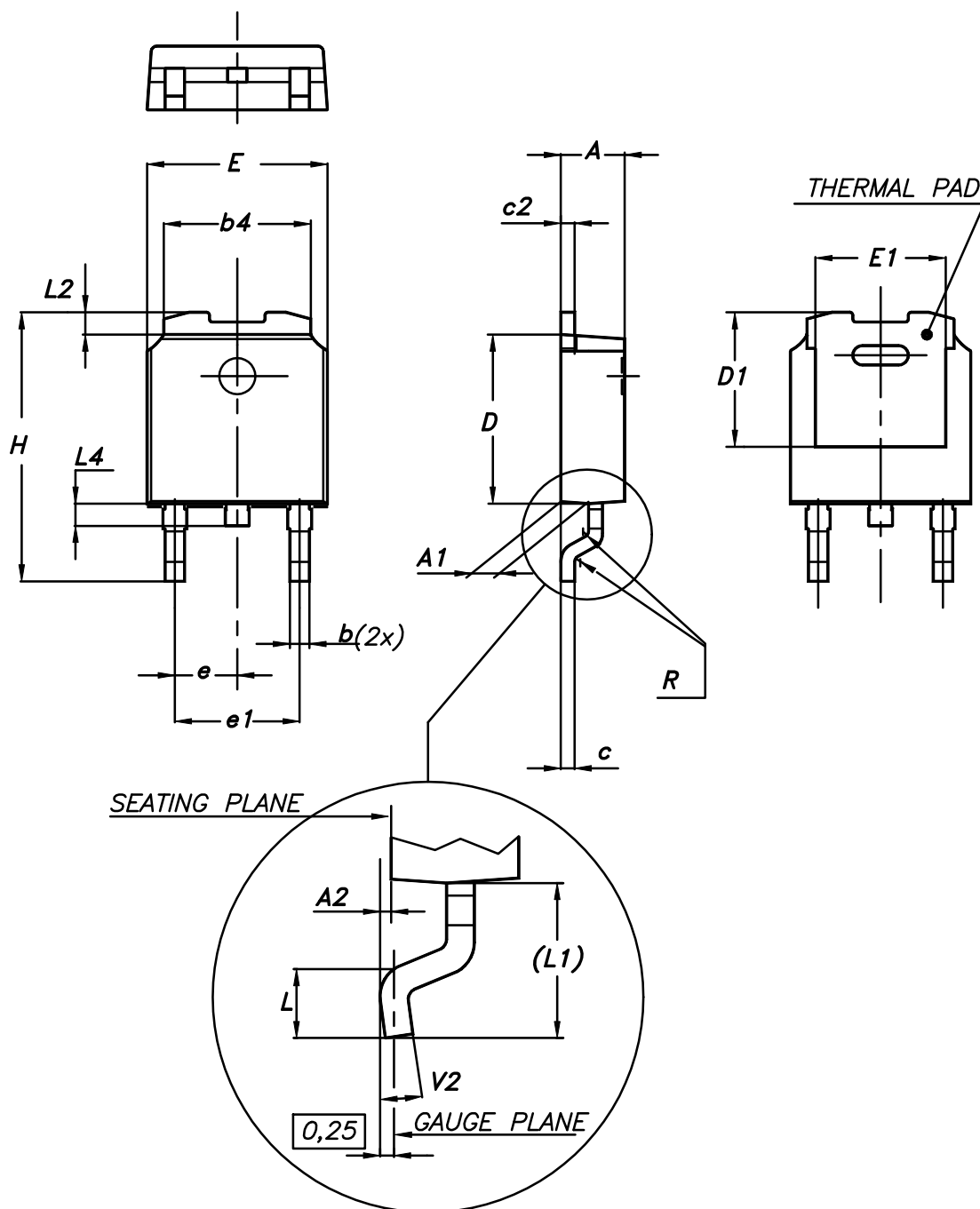
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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 DPAK (TO-252) type A package information

Figure 21. DPAK (TO-252) type A package outline



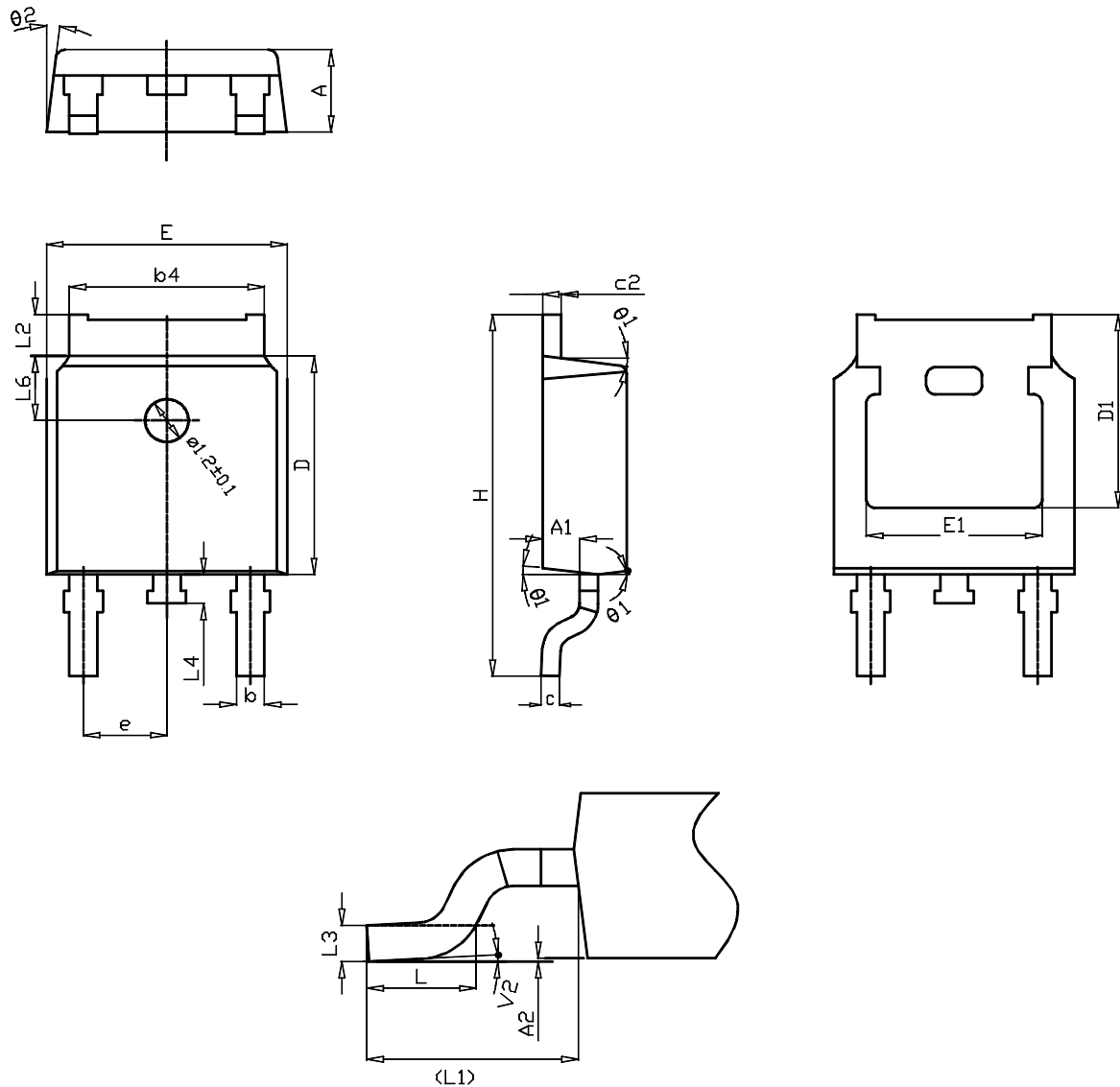
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Table 8. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	4.60	4.70	4.80
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
(L1)	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

4.2 DPAK (TO-252) type C package information

Figure 22. DPAK (TO-252) type C package outline



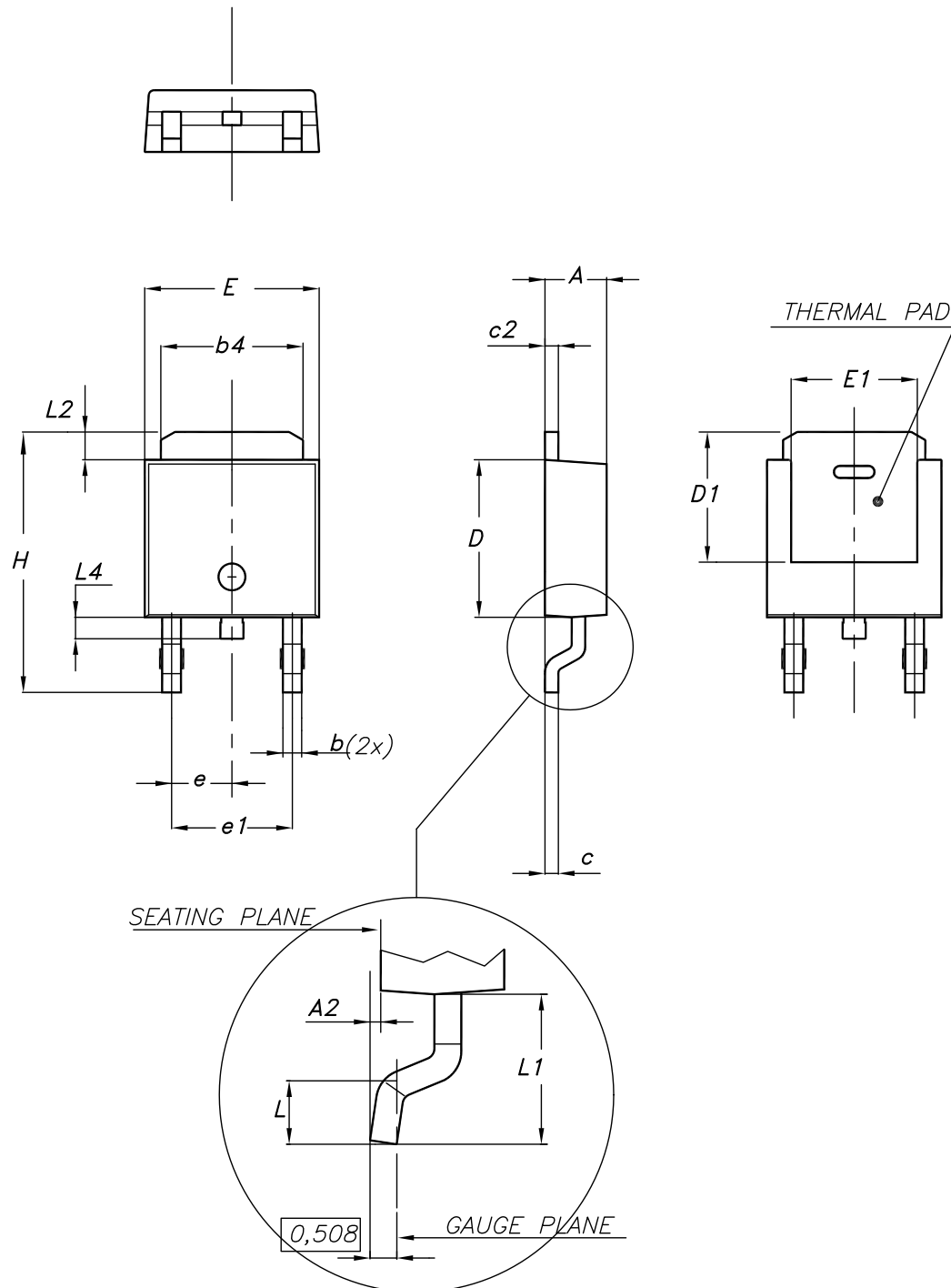
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Table 9. DPAK (TO-252) type C mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.38
A1	0.90	1.01	1.10
A2	0.00		0.10
b	0.72		0.85
b4	5.13	5.33	5.46
c	0.47		0.60
c2	0.47		0.60
D	6.00	6.10	6.20
D1	5.25		
E	6.50	6.60	6.70
E1	4.70		
e	2.186	2.286	2.386
H	9.80	10.10	10.40
L	1.40	1.50	1.70
L1	2.90 REF		
L2	0.90		1.25
L3	0.51 BSC		
L4	0.60	0.80	1.00
L6	1.80 BSC		
θ1	5°	7°	9°
θ2	5°	7°	9°
V2	0°		8°

4.3 DPAK (TO-252) type E package information

Figure 23. DPAK (TO-252) type E package outline

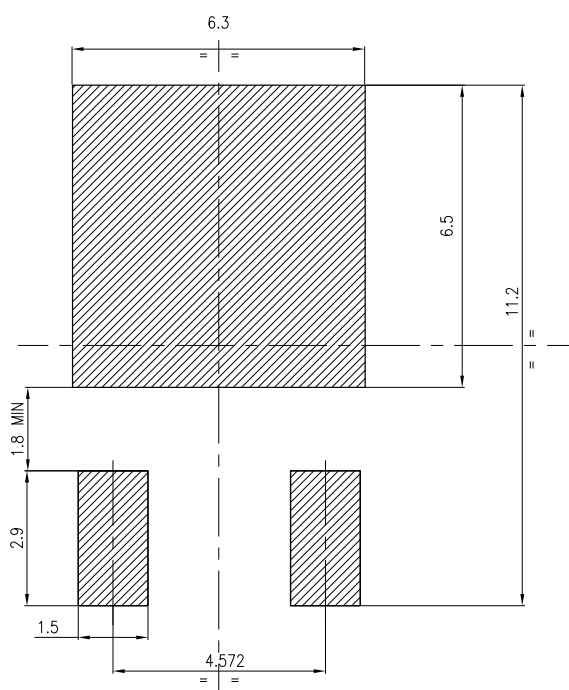


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Table 10. DPAK (TO-252) type E mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.18		2.39
A2			0.13
b	0.65		0.884
b4	4.95		5.46
c	0.46		0.61
c2	0.46		0.60
D	5.97		6.22
D1	5.21		
E	6.35		6.73
E1	4.32		
e		2.286	
e1		4.572	
H	9.94		10.34
L	1.50		1.78
L1		2.74	
L2	0.89		1.27
L4			1.02

Figure 24. DPAK (TO-252) recommended footprint (dimensions are in mm)



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4.4 DPAK (TO-252) packing information

Figure 25. DPAK (TO-252) tape outline

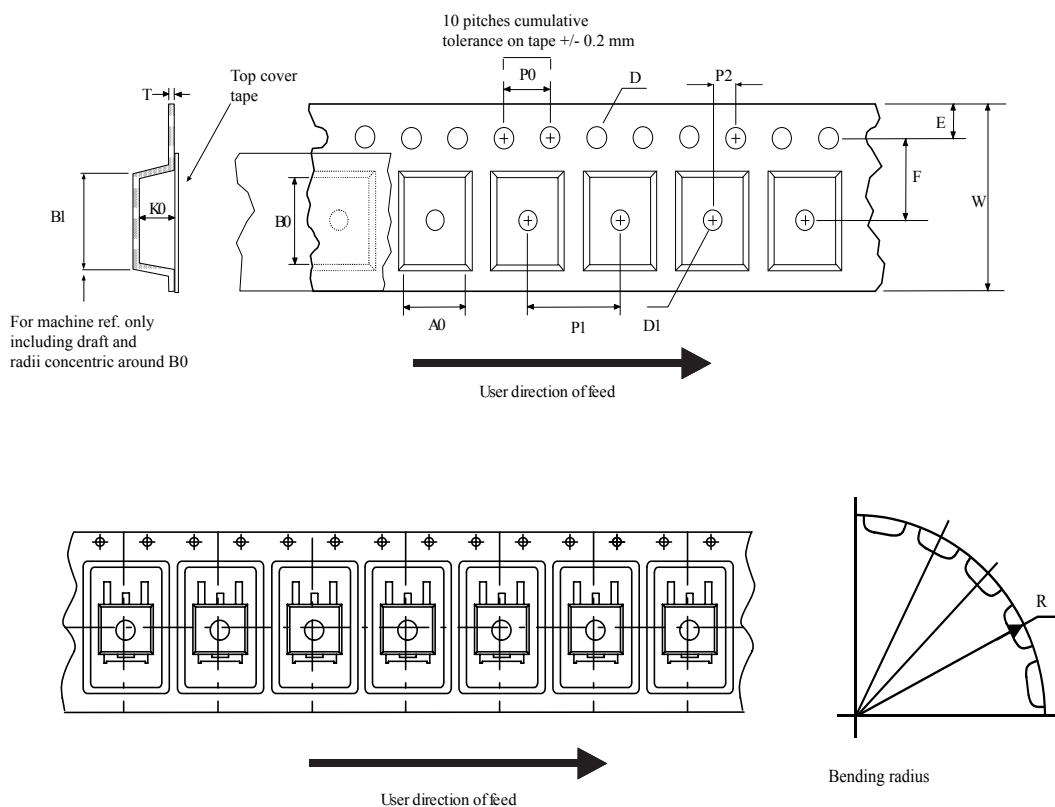
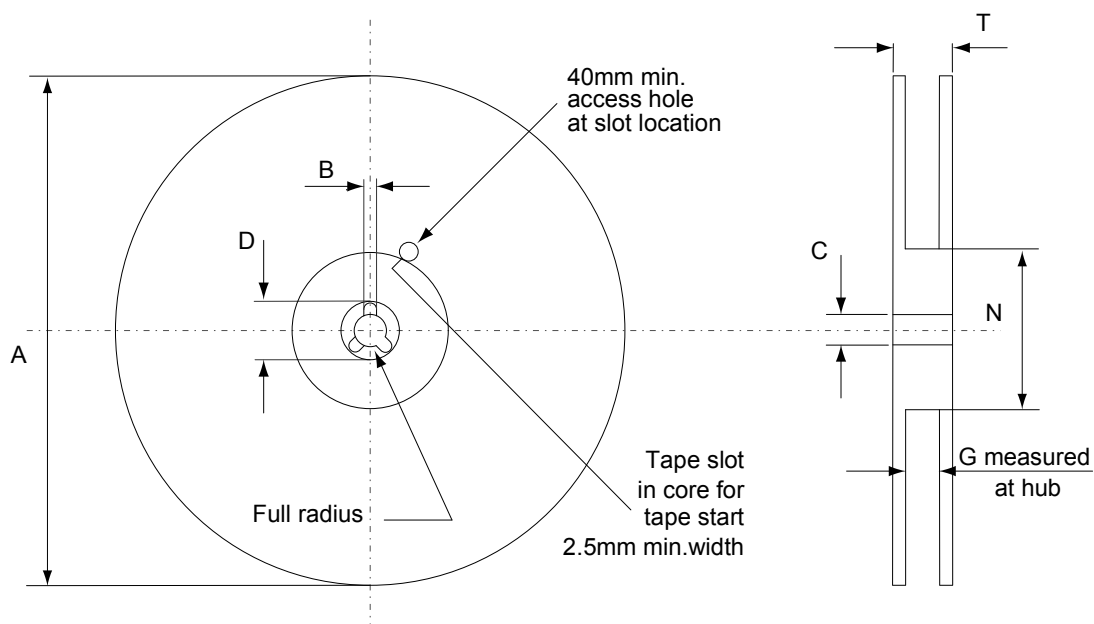


Figure 26. DPAK (TO-252) reel outline


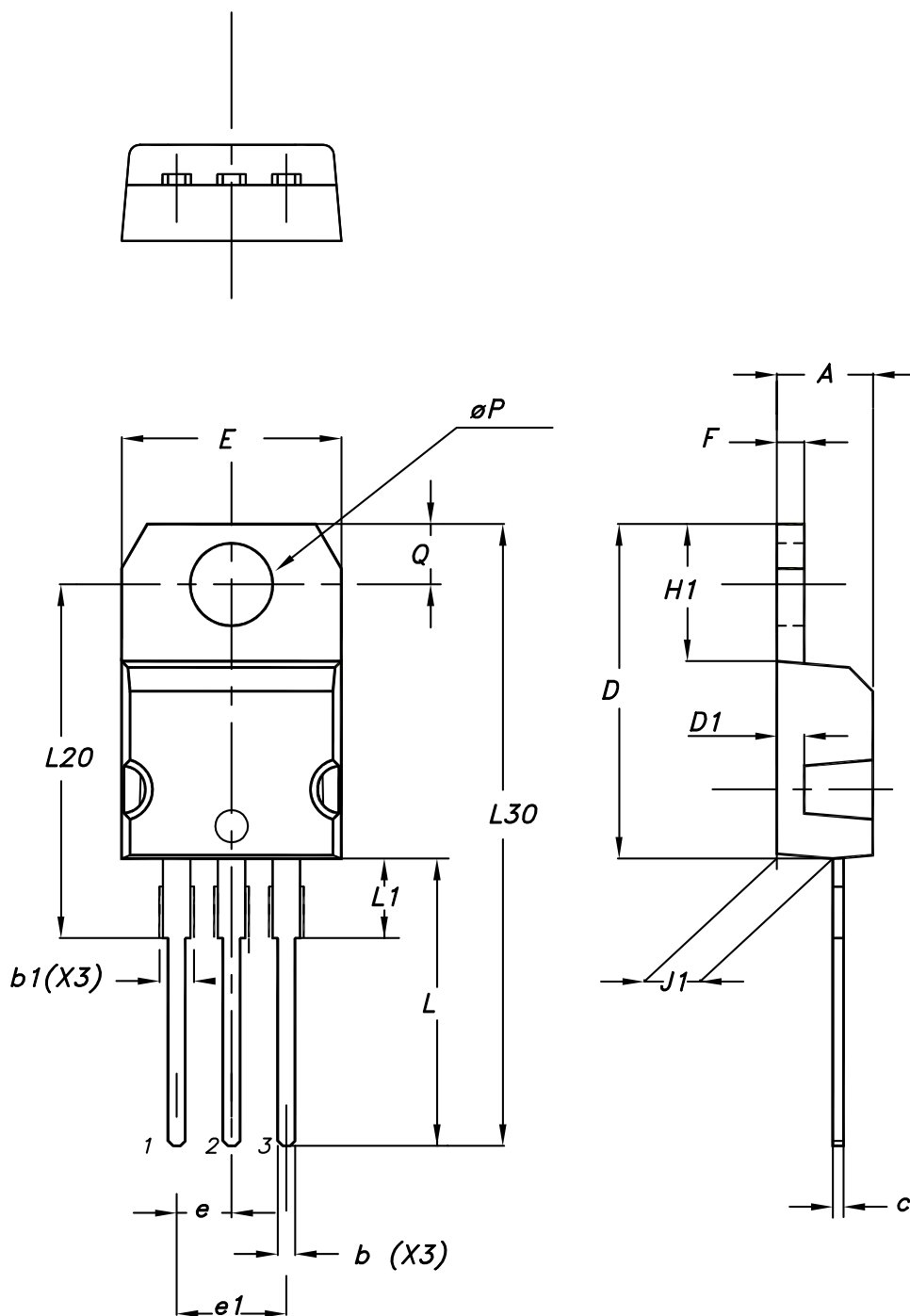
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Table 11. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

4.5 TO-220 type A package information

Figure 27. TO-220 type A package outline



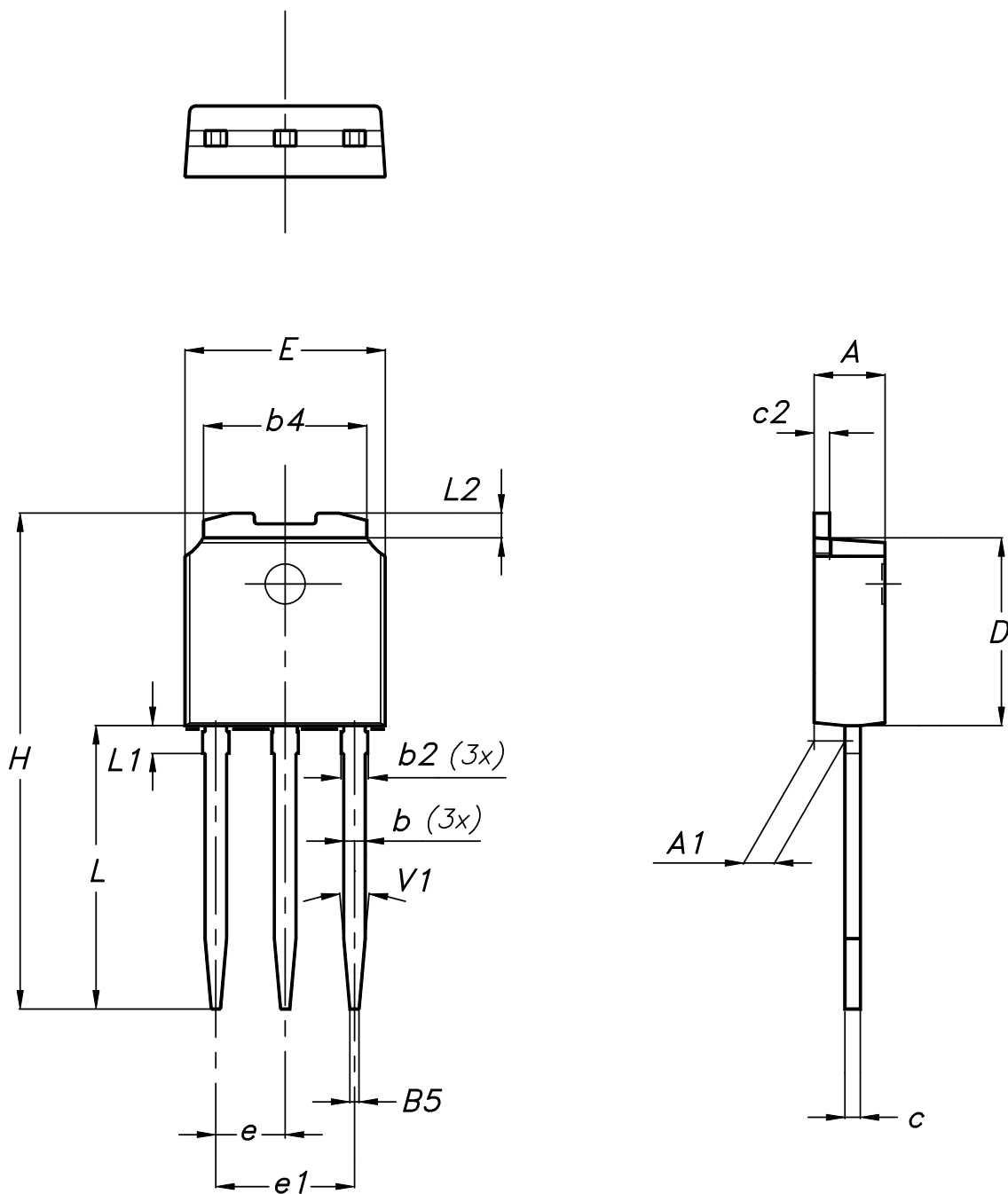
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Table 12. TO-220 type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95

4.6 IPAK (TO-251) type A package information

Figure 28. IPAK (TO-251) type A package outline



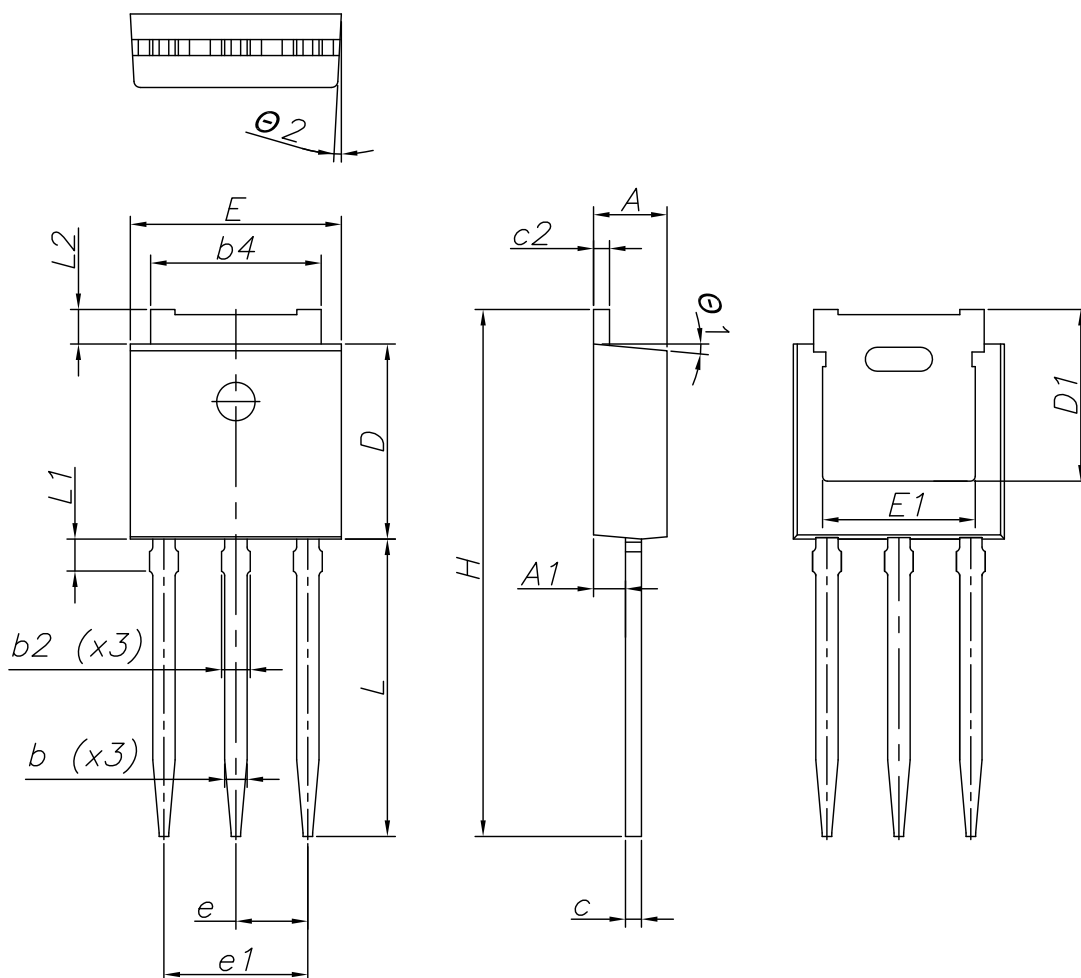
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Table 13. IPAK (TO-251) type A package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

4.7 IPAK (TO-251) type C package information

Figure 29. IPAK (TO-251) type C package outline



0068771_IK_typeC_rev14

Table 14. IPAK (TO-251) type C package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20	2.30	2.35
A1	0.90	1.00	1.10
b	0.66		0.79
b2			0.90
b4	5.23	5.33	5.43
c	0.46		0.59
c2	0.46		0.59
D	6.00	6.10	6.20
D1	5.20	5.37	5.55
E	6.50	6.60	6.70
E1	4.60	4.78	4.95
e	2.20	2.25	2.30
e1	4.40	4.50	4.60
H	16.18	16.48	16.78
L	9.00	9.30	9.60
L1	0.80	1.00	1.20
L2	0.90	1.08	1.25
θ1	3°	5°	7°
θ2	1°	3°	5°

5 Ordering information

Table 15. Ordering information

Order code	Marking	Package	Packing
STD11N65M2	11N65M2	DPAK	Tape and reel
STP11N65M2		TO-220	Tube
STU11N65M2		IPAK	

Revision history

Table 16. Document revision history

Date	Revision	Changes
16-May-2014	1	First release.
14-Aug-2015	2	Text and formatting changes throughout document. On cover page: - updated <i>Title, Features and Description</i> In section <i>Electrical characteristics</i> : - updated and renamed table <i>Static</i> (was On /off states) Updated section <i>Electrical characteristics (curves)</i> Updated and renamed section <i>Package information</i> (was Package mechanical data)
17-Aug-2015	3	Datasheet promoted from preliminary data to production data. In section <i>Electrical ratings</i> : - updated and renamed table <i>Absolute maximum ratings</i> In section <i>Electrical characteristics</i> : - updated table <i>Source-drain diode</i> In section <i>Electrical characteristics (curves)</i> - updated figure <i>Thermal impedance for DPAK and IPAK</i> Updated and renamed section <i>IPAK (TO-251) Type C package information</i> (was IPAK (TO-251) Type A package information)
07-Sep-2015	4	Minor text and formatting changes throughout document.
16-Oct-2018	5	Updated Section 4 Package information . Minor text changes.
18-Jun-2019	6	Updated Section 3 Minor text changes.

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Данный компонент на территории Российской Федерации

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Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

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